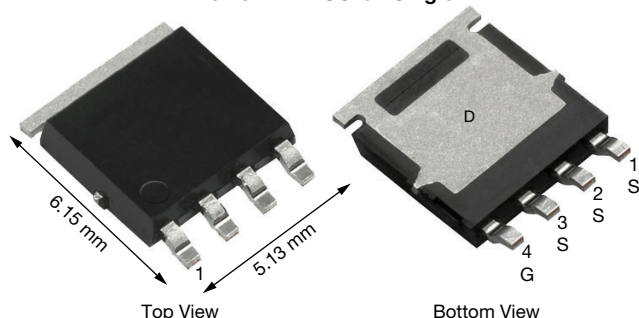


N-Channel 40 V (D-S) MOSFET

PRODUCT SUMMARY

V _{DS} (V)	R _{DS(on)} (Ω) Max.	I _D (A) ^{a, g}	Q _g (Typ.)
40	0.00235 at V _{GS} = 10 V	60	32 nC
	0.00320 at V _{GS} = 4.5 V	60	

PowerPAK® SO-8L Single



Ordering Information:

SiJA54DP-T1-GE3 (lead (Pb)-free and halogen-free)

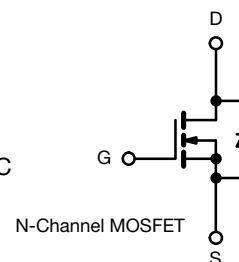
FEATURES

- TrenchFET® Gen IV power MOSFET
- Tuned for the lowest R_{DS}-Q_{oss} FOM
- 100 % R_g and UIS tested
- Q_{gd} / Q_{gs} ratio < 1 optimizes switching characteristics
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912


RoHS
COMPLIANT
HALOGEN
FREE

APPLICATIONS

- Synchronous rectification
- ORing
- High power density DC/DC
- VRMs and embedded DC/DC
- DC/AC inverters
- Load switch



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C, unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	40	V
Gate-Source Voltage	V _{GS}	+20, -16	
Continuous Drain Current (T _J = 150 °C)	I _D	T _C = 25 °C	60 ^g
		T _C = 70 °C	60 ^g
		T _A = 25 °C	32.2 ^{b, c}
		T _A = 70 °C	25.7 ^{b, c}
Pulsed Drain Current (t = 100 μs)	I _{DM}	150	A
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C	
		T _A = 25 °C	
Single Pulse Avalanche Current	I _{AS}	30	
Single Pulse Avalanche Energy	E _{AS}	45	mJ
Maximum Power Dissipation	P _D	T _C = 25 °C	36.7
		T _C = 70 °C	23.5
		T _A = 25 °C	4.4 ^{b, c}
		T _A = 70 °C	2.8 ^{b, c}
Operating Junction and Storage Temperature Range	T _J , T _{stg}	-55 to +150	°C
Soldering Recommendations (Peak Temperature) ^{d, e}		260	

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^{b, f}	R _{thJA}	24	28	°C/W
Maximum Junction-to-Case (Drain)	R _{thJC}	2.5	3.4	

Notes

- T_C = 25 °C.
- Surface mounted on 1" x 1" FR4 board.
- t = 10 s.
- See solder profile (www.vishay.com/doc?773257). The PowerPAK SO-8L is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.
- Maximum under steady state conditions is 70 °C/W.
- Package limited.



SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA	40	-	-	V
V _{DS} Temperature Coefficient	ΔV _{DS} /T _J	I _D = 250 μA	-	24	-	mV/°C
V _{GS(th)} Temperature Coefficient	ΔV _{GS(th)} /T _J		-	-5.2	-	
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	1.1	-	2.4	V
Gate-Source Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = +20 V, -16 V	-	-	± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 40 V, V _{GS} = 0 V	-	-	1	μA
		V _{DS} = 40 V, V _{GS} = 0 V, T _J = 55 °C	-	-	10	
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≥ 5 V, V _{GS} = 10 V	30	-	-	A
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V, I _D = 15 A	-	0.00195	0.00235	Ω
		V _{GS} = 4.5 V, I _D = 10 A	-	0.00265	0.00320	
Forward Transconductance ^a	g _{fs}	V _{DS} = 10 V, I _D = 15 A	-	106	-	S
Dynamic ^b						
Input Capacitance	C _{iss}	V _{DS} = 20 V, V _{GS} = 0 V, f = 1 MHz	-	5300	-	pF
Output Capacitance	C _{oss}		-	707	-	
Reverse Transfer Capacitance	C _{rss}		-	105	-	
Total Gate Charge	Q _g	V _{DS} = 20 V, V _{GS} = 10 V, I _D = 10 A	-	69	104	nC
		V _{DS} = 20 V, V _{GS} = 4.5 V, I _D = 10 A	-	32	48	
Q _{gs}	-		13.5	-		
Q _{gd}	-		6.9	-		
Q _{oss}	-	30.5	46			
Gate Resistance	R _g	f = 1 MHz	0.4	1.1	2.0	Ω
Turn-On Delay Time	t _{d(on)}	V _{DD} = 20 V, R _L = 2 Ω I _D ≅ 10 A, V _{GEN} = 10 V, R _g = 1 Ω	-	8	16	ns
Rise Time	t _r		-	8	16	
Turn-Off Delay Time	t _{d(off)}		-	28	56	
Fall Time	t _f		-	7	14	
Turn-On Delay Time	t _{d(on)}	V _{DD} = 20 V, R _L = 2 Ω I _D ≅ 10 A, V _{GEN} = 4.5 V, R _g = 1 Ω	-	24	48	
Rise Time	t _r		-	69	138	
Turn-Off Delay Time	t _{d(off)}		-	23	46	
Fall Time	t _f		-	10	20	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C	-	-	33.3	A
Pulse Diode Forward Current (t = 100 μs)	I _{SM}		-	-	150	
Body Diode Voltage	V _{SD}	I _S = 5 A	-	0.72	1.1	V
Body Diode Reverse Recovery Time	t _{rr}	I _F = 10 A, dI/dt = 100 A/μs, T _J = 25 °C	-	44	88	ns
Body Diode Reverse Recovery Charge	Q _{rr}		-	58	116	nC
Reverse Recovery Fall Time	t _a		-	29	-	ns
Reverse Recovery Rise Time	t _b		-	15	-	

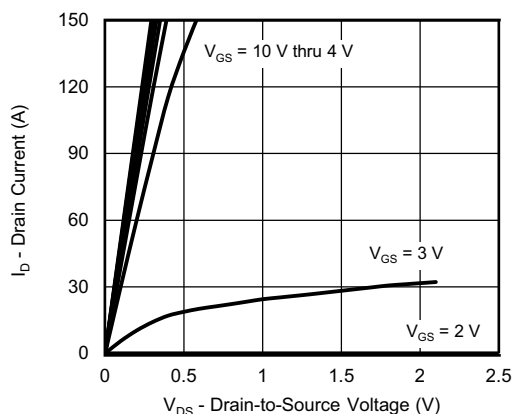
Notes

- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
b. Guaranteed by design, not subject to production testing.

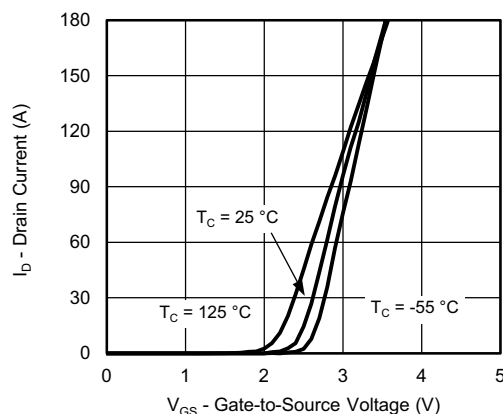
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



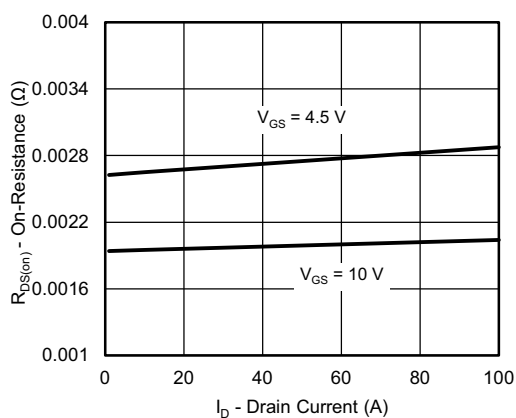
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



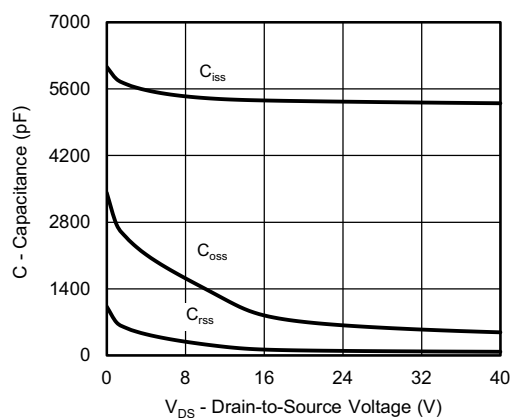
Output Characteristics



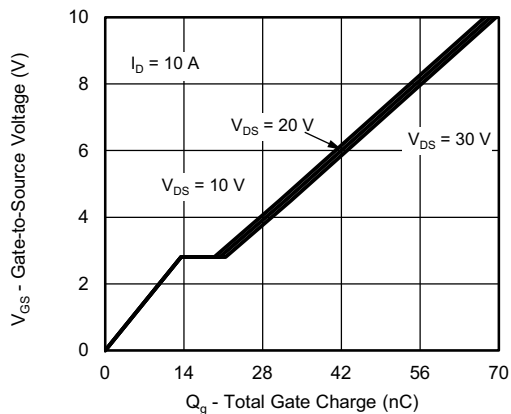
Transfer Characteristics



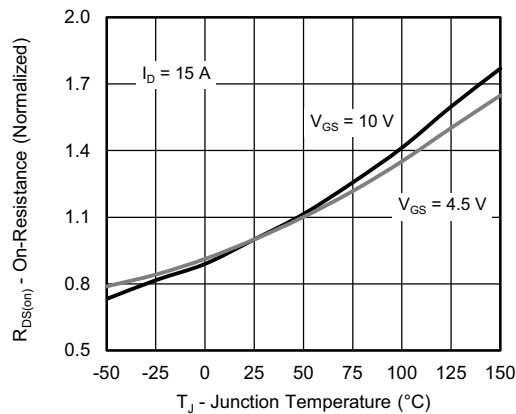
On-Resistance vs. Drain Current



Capacitance



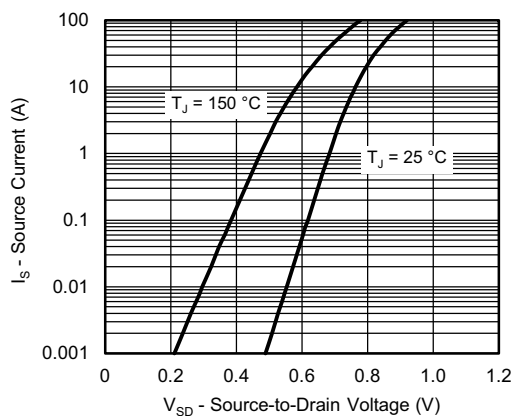
Gate Charge



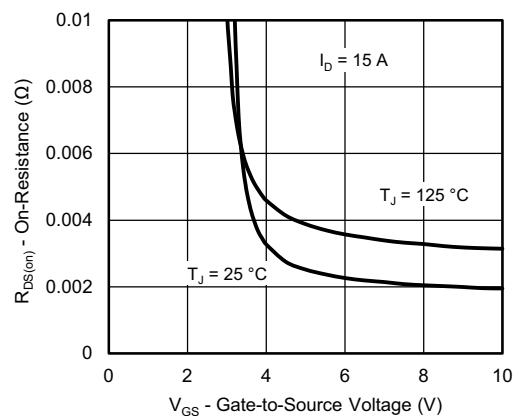
On-Resistance vs. Junction Temperature



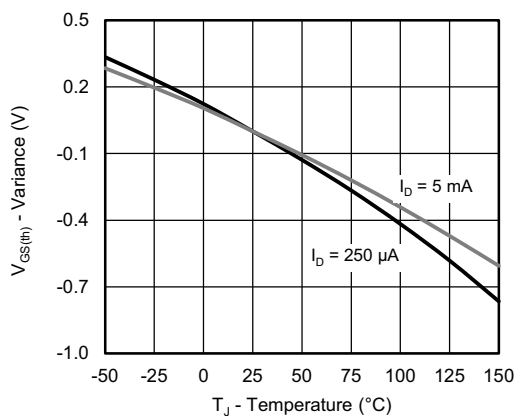
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



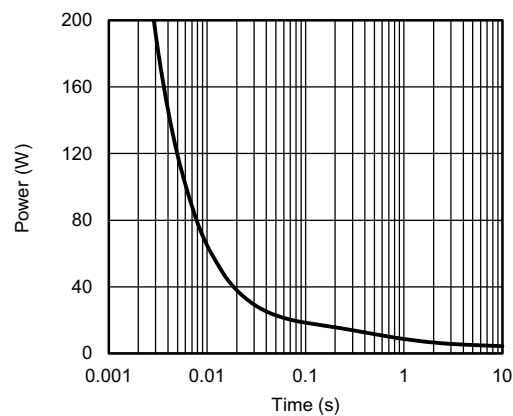
Source-Drain Diode Forward Voltage



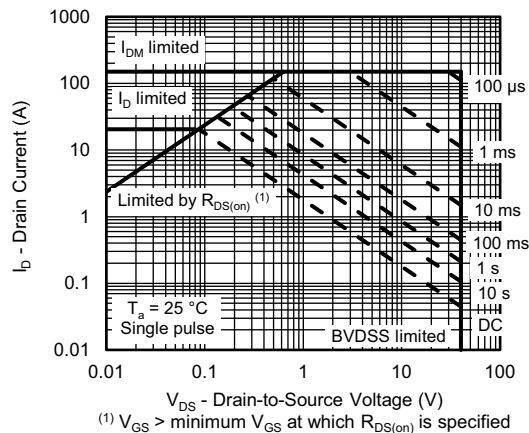
On-Resistance vs. Gate-to-Source Voltage



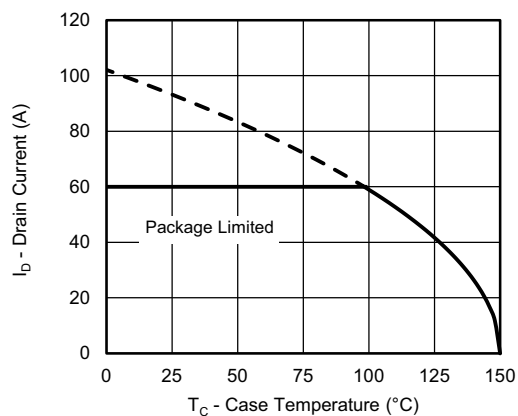
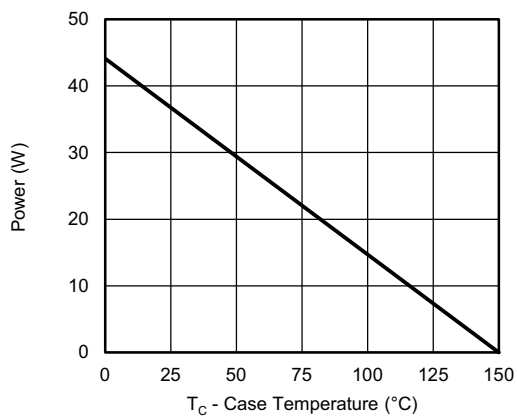
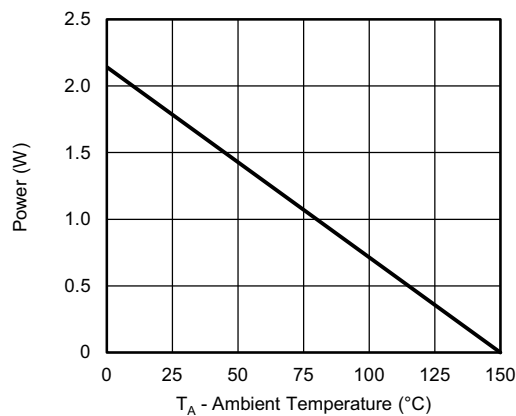
Threshold Voltage



Single Pulse Power, Junction-to-Ambient



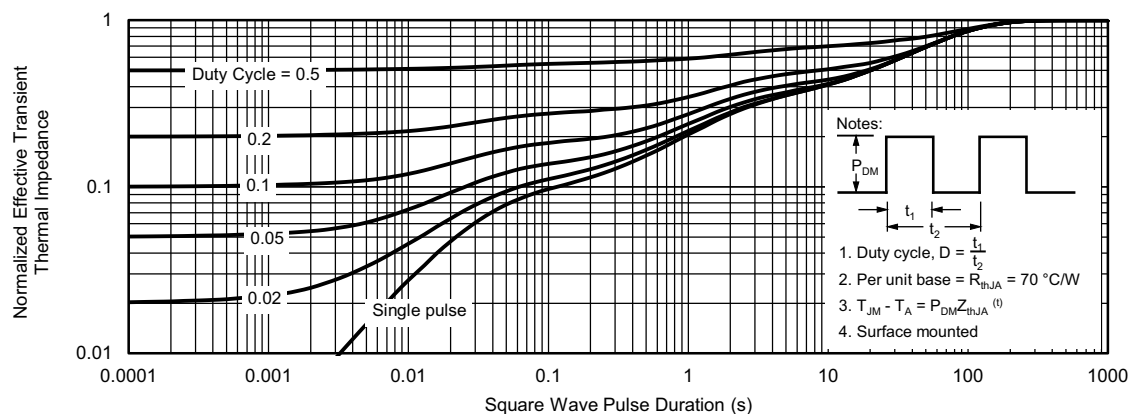
Safe Operating Area, Junction-to-Ambient

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Current Derating ^a

Power, Junction-to-Case

Power, Junction-to-Ambient
Note

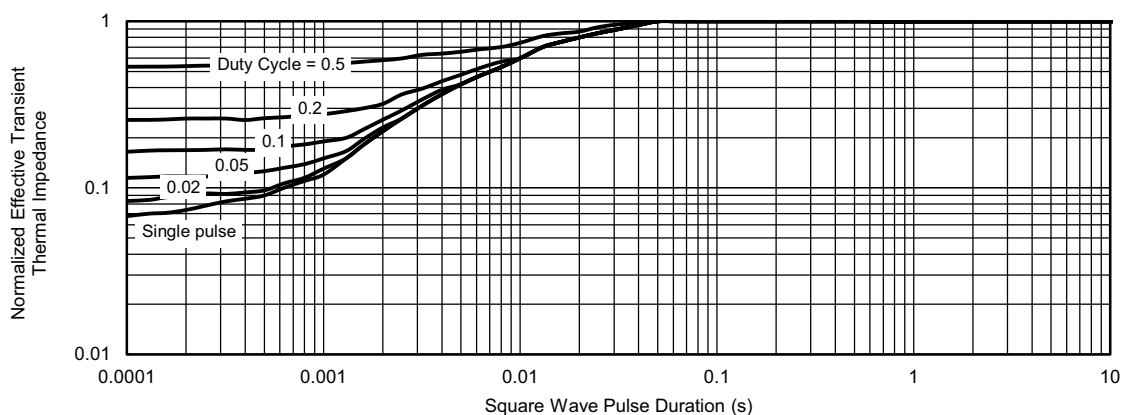
- a. The power dissipation P_D is based on T_J (max.) = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient

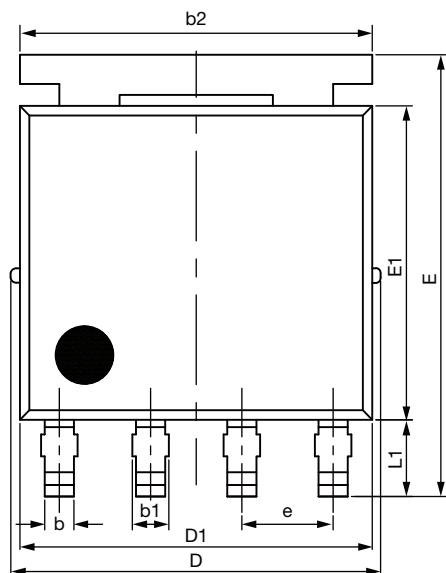


Normalized Thermal Transient Impedance, Junction-to-Case

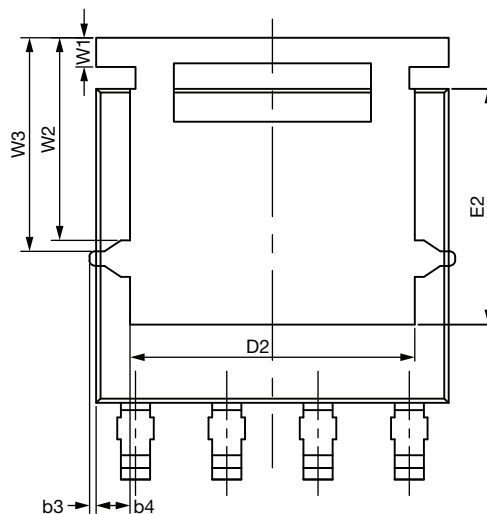
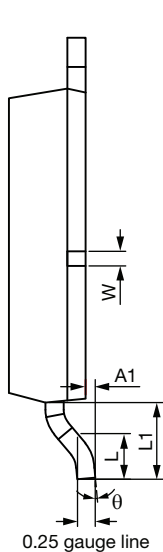
Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?67424.



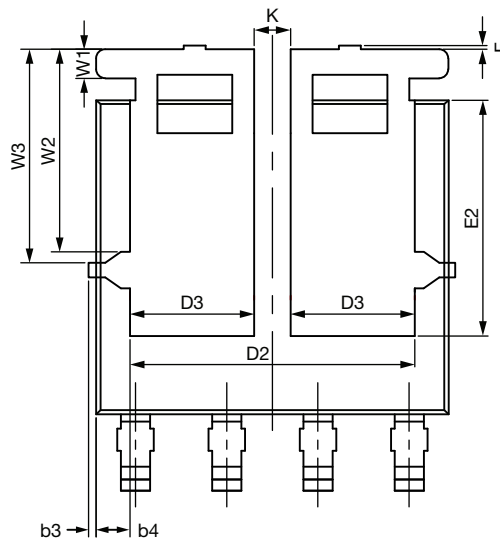
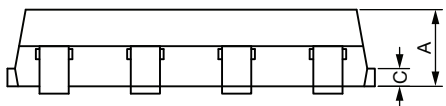
PowerPAK® SO-8L Case Outline for Non-AI Parts



Topside view



Backside view (single)



Backside view (dual)



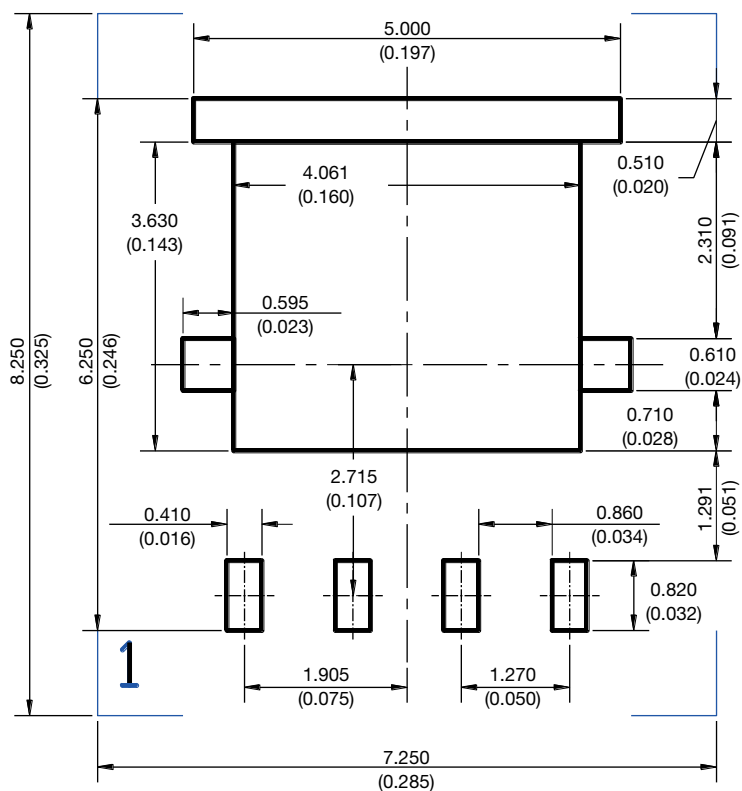
DIM.	MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	1.00	1.07	1.14	0.039	0.042	0.045
A1	0.00	-	0.127	0.00	-	0.005
b	0.33	0.41	0.48	0.013	0.016	0.019
b1	0.44	0.51	0.58	0.017	0.020	0.023
b2	4.80	4.90	5.00	0.189	0.193	0.197
b3	0.094			0.004		
b4	0.47			0.019		
c	0.20	0.25	0.30	0.008	0.010	0.012
D	5.00	5.13	5.25	0.197	0.202	0.207
D1	4.80	4.90	5.00	0.189	0.193	0.197
D2	3.86	3.96	4.06	0.152	0.156	0.160
D3	1.63	1.73	1.83	0.064	0.068	0.072
e	1.27 BSC			0.050 BSC		
E	6.05	6.15	6.25	0.238	0.242	0.246
E1	4.27	4.37	4.47	0.168	0.172	0.176
E2	3.18	3.28	3.38	0.125	0.129	0.133
F	-	-	0.15	-	-	0.006
L	0.62	0.72	0.82	0.024	0.028	0.032
L1	0.92	1.07	1.22	0.036	0.042	0.048
K	0.51			0.020		
W	0.23			0.009		
W1	0.41			0.016		
W2	2.82			0.111		
W3	2.96			0.117		
θ	0°	-	10°	0°	-	10°
ECN: T16-0221-Rev. D, 16-May-16						
DWG: 5976						

Note

- Millimeters will govern



RECOMMENDED MINIMUM PAD FOR PowerPAK® SO-8L SINGLE



Recommended Minimum Pads
Dimensions in mm (inches)



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